SEMICONDUCTOR

# 2N5772

## **NPN Switching Transistor**

• Sourced from process 22.



1. Emitter 2. Base 3. Collector

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## Absolute Maximum Ratings \* T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units	
CEO	Collector-Emitter Voltage	15	V	
сво	Collector-Base Voltage	40	V	
Ево	Emitter-Base Voltage	5.0	V	
0	Collector Current - Continued	300	mA	
STG	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C	

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

## Electrical Characteristics $T_a=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Charact	eristics	•		•	
BV <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage *	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$	15		V
BV(BR)CES	Collector-Emitter Breakdown Voltage	$I_{C} = 100\mu A, V_{BE} = 0$	40		V
BV <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \mu {\rm A}, I_{\rm E} = 0$	40		V
BV <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{\rm E} = 100 \mu A, I_{\rm C} = 0$	5.0		V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 20V, I_E = 0$		0.5	μA
CES	Collector Cutoff Current	$V_{CE} = 20V, V_{BE} = 0$		0.5	μΑ
		$V_{CE} = 20V, V_{BE} = 0, T_a = 65^{\circ}C$		3.0	μΑ
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 5.0V, I_{C} = 0$		100	μΑ
On Charact	eristics *				
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 0.4 V, I_{C} = 30 mA$	30	120	
		$V_{CE} = 0.5V, I_{C} = 100mA$	25		
		$V_{CE} = 1.0V, I_{C} = 300mA$	15		
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 30mA, I <sub>B</sub> = 3.0mA		0.2	V
		$I_{\rm C} = 100 {\rm mA}, I_{\rm B} = 10 {\rm mA}$		0.28	V
		I <sub>C</sub> = 300mA, I <sub>B</sub> = 3.0mA		0.5	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = 30mA, I <sub>B</sub> = 3.0mA	0.73	0.95	V
		I <sub>C</sub> = 100mA, I <sub>B</sub> = 10mA		1.2	V
		I <sub>C</sub> = 300mA, I <sub>B</sub> = 3.0mA		1.7	V
Small Signa	al Characteristics				
C <sub>cb</sub>	Collector-Base Capacitance	$V_{CB} = 5.0V, I_E = 0, f = 1MHz$		5.0	pF
C <sub>eb</sub>	Emitter-Base Capacitance	$V_{CB} = 5.0V, I_{C} = 0, f = 1MHz$		8.0	pF
h <sub>fe</sub>	Small-Signal Current Gain	I <sub>C</sub> = 300mA, V <sub>CE</sub> = 10V, f = 100MHz	3.5		

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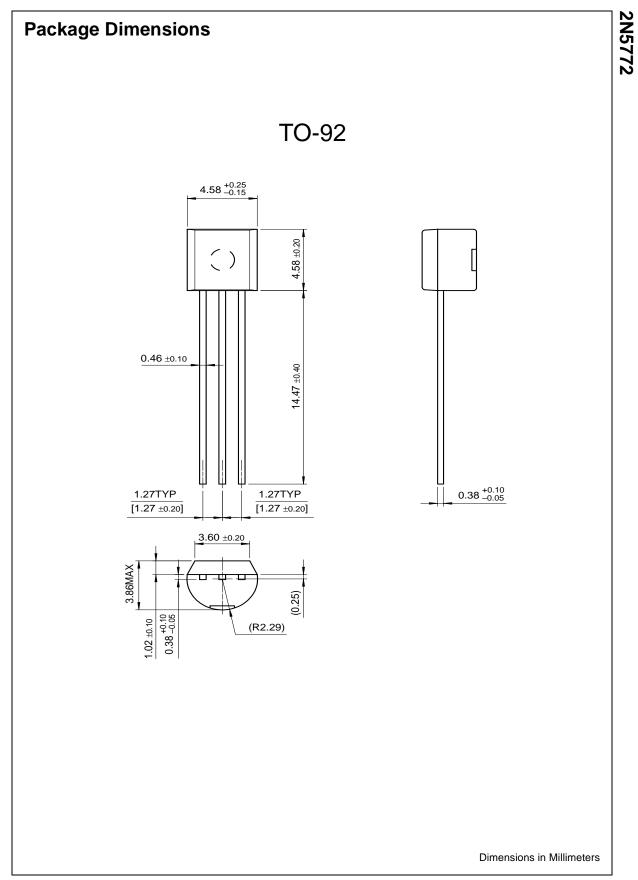
# Electrical Characteristics Ta=25°C unless otherwise noted (Continued)

Symbol	Parameter	Test Condition	Min.	Max.	Units
Switching Characteristics					
t <sub>s</sub>	Storage Time	I <sub>C</sub> = 300mA, V <sub>CC</sub> = 10V		20	ns
t <sub>on</sub>	Turn-On Time	I <sub>B1</sub> = I <sub>B2</sub> = 30mA		18	ns
t <sub>off</sub>	Turn-Off Time			28	ns

## Thermal Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Max.	Units	
PD	Total Device Dissipation	350	mW	
	Derate above 25°C	2.8	mW/°C	
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case	125	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W	

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